General Purpose Transistors

NPN Bipolar Junction Transistor

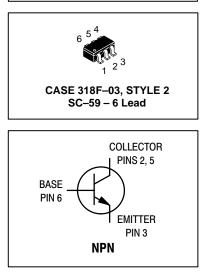
(Complementary PNP Device: MMBT2131T1/T3)

MAXIMUM RATINGS (T_C = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	30	V
Collector–Base Voltage	VCBO	40	V
Emitter-Base Voltage	VEBO	5.0	V
Collector Current	IC	700	mA
Base Current	۱ _B	350	mA
Total Power Dissipation @ $T_C = 25^{\circ}C$ Total Power Dissipation @ $T_C = 85^{\circ}C$ Thermal Resistance – Junction to Ambient (1)	PD PD R _θ JA	342 178 366	mW mW °C/W
Total Power Dissipation @ $T_C = 25^{\circ}C$ Total Power Dissipation @ $T_C = 85^{\circ}C$ Thermal Resistance – Junction to Ambient (2)	P _D P _D R _{θJA}	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	TJ, Tstg	-55 to +150	°C



0.7 AMPERES 30 VOLTS – V(BR)CEO 342 mW



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit		
OFF CHARACTERISTICS							
Collector–Base Breakdown Voltage (I _C = 100 µAdc)		40	-	-	Vdc		
Collector–Emitter Breakdown Voltage (I _C =	10 mAdc) V(BR)CEO) 30	-	-	Vdc		
Emitter–Base Breakdown Voltage (IE = 2	00 μAdc) V(BR)EBO	5.0	-	-	Vdc		
Collector Cutoff Current $(V_{CB} = 25 \text{ Vdc}, I_E = 0 \text{ Adc}, T_A (V_{CB} = 25 \text{ Vdc}, I_E = 0 \text{ Adc}, T_$				1.0 10	μAdc		
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C	; = 0 Adc) I _{EBO}	-	-	10	μAdc		

ON CHARACTERISTICS

DC Current Gain $(V_{CE} = 3.0 \text{ Vdc}, I_C = 10)$		hFE	150	-	-	Vdc
Collector–Emitter Saturation Voltage $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ m/s})$		V _{CE(sat)}	-	-	0.25	Vdc
Collector–Emitter Saturation Voltage	$(I_C = 700 \text{ mAdc}, I_B = 70 \text{ mAdc})$	V _{CE(sat)}	-	-	0.4	Vdc
Base–Emitter Saturation Voltage $(I_C = 700 \text{ mAdc}, I_B = 70 \text{ mAdc})$		V _{BE(sat)}	-	-	1.1	Vdc
Collector–Emitter Saturation Voltage	$(I_{C} = 700 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	V _{BE(on)}	-	-	1.0	Vdc

1. Minimum FR-4 or G-10 PCB, Operating to Steady State.

2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.

MMBT2132T1 MMBT2132T3

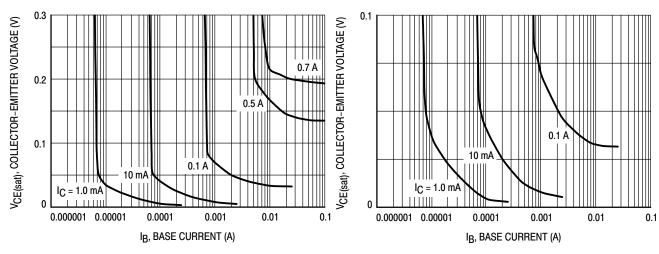
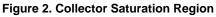


Figure 1. Collector Saturation Region



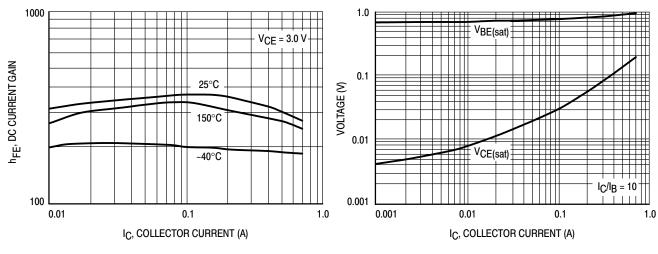


Figure 3. DC Current Gain

Figure 4. "ON" Voltages

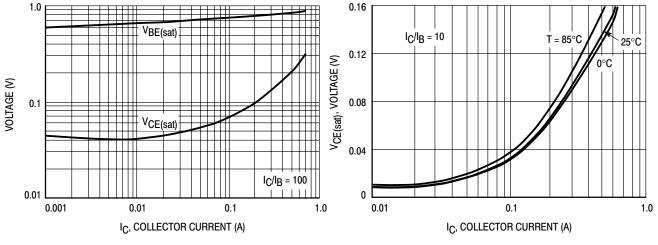


Figure 5. "ON" Voltages

Figure 6. Collector–Emitter Saturation Voltage

MMBT2132T1 MMBT2132T3

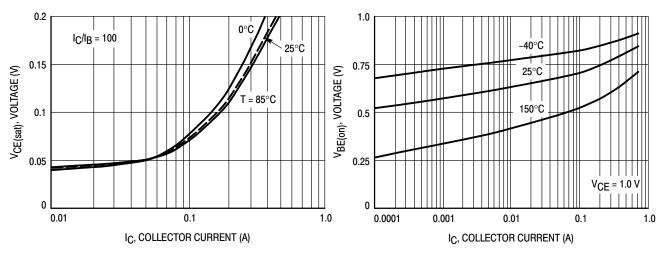




Figure 8. VBE(on) Voltage

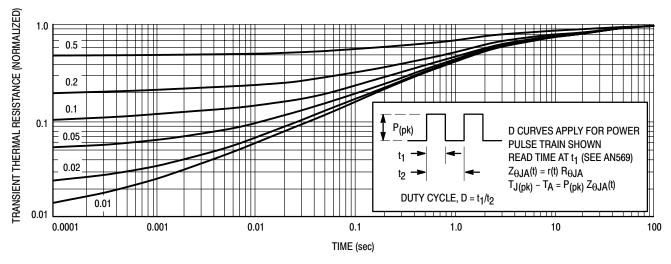
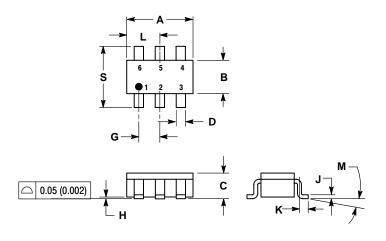


Figure 9. Thermal Response Curve

PACKAGE DIMENSIONS

SC-74 CASE 318F-03 ISSUE F





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI X14 5M 1982

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

4. 318F-01 AND -02 OBSOLETE. NEW STANDARD 318F-03.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1142	0.1220	2.90	3.10
В	0.0512	0.0669	1.30	1.70
C	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
Н	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
K	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
Μ	0 °	10 °	0 °	10 °
S	0.0985	0.1181	2.50	3.00

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